

ATTACHMENT A: SEARCH HISTORY

L Number	Hits	Search Text	DB	Time stamp
9	25542	memory and cell and transistors and (threshold same voltage)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/01 02:07
10	1905	(memory and cell and transistors and (threshold same voltage)) and (power same line) and (storage same node)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/01 02:08
11	5487	"11" and (virtual same ground)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/01 02:08
12	61	((memory and cell and transistors and (threshold same voltage)) and (power same line) and (storage same node)) and (virtual same ground)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/01 02:08
13	4	((memory and cell and transistors and (threshold same voltage)) and (power same line) and (storage same node)) and (virtual same ground)) and subthreshold	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/01 02:09
14	0	((memory and cell and transistors and (threshold same voltage)) and (power same line) and (storage same node)) and (virtual same ground)) and superthreshold	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/01 02:09
15	41	((memory and cell and transistors and (threshold same voltage)) and (power same line) and (storage same node)) and (virtual same ground)) and (mode same operation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/01 02:09
16	2	((memory and cell and transistors and (threshold same voltage)) and (power same line) and (storage same node)) and (virtual same ground)) and subthreshold) and (((memory and cell and transistors and (threshold same voltage)) and (power same line) and (storage same node)) and (virtual same ground)) and (mode same operation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/01 02:10
17	37	((memory and cell and transistors and (threshold same voltage)) and (power same line) and (storage same node)) and (virtual same ground)) and (mode same operation)) and 365/\$7.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/01 02:10